

Abstract Submitted  
for the MAR14 Meeting of  
The American Physical Society

**Topological insulator nanowires and nanowire hetero-junctions<sup>1</sup>**

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<sup>1</sup>Supported in part by NSF-DMR-1122594, NSF-DMR-1312483-MWN, and DOD-W911NF-13-1-0159

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Date submitted: 15 Nov 2013

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